

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U3900-GSM850-251CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 62.15 V/m; Power Drift = -0.05 dB

PMF = 2.830 is applied.

E-field emissions = 138.3 V/m

Near-field category: M4 (AWF -5 dB)

PMF scaled E-field

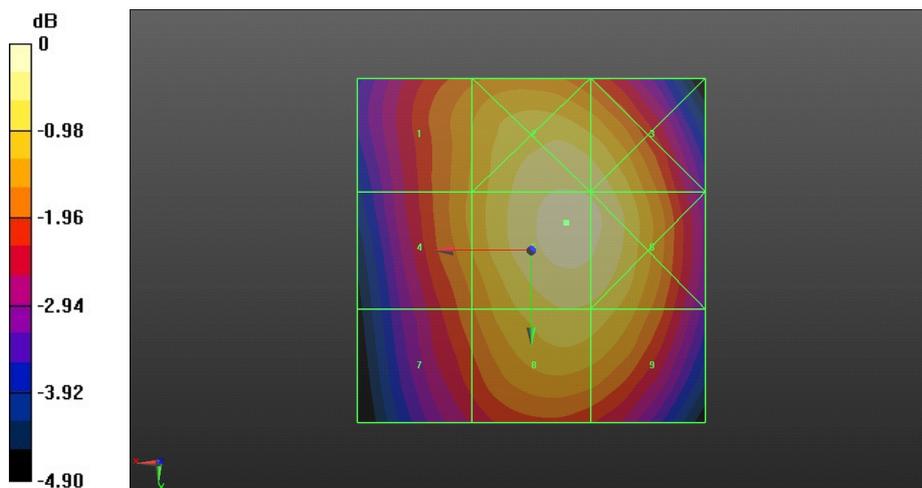
Grid 1 M4 122.3 V/m	Grid 2 M4 136.0 V/m	Grid 3 M4 135.1 V/m
Grid 4 M4 122.9 V/m	Grid 5 M4 138.3 V/m	Grid 6 M4 137.3 V/m
Grid 7 M4 116.2 V/m	Grid 8 M4 130.6 V/m	Grid 9 M4 129.7 V/m

Cursor:

Total = 138.3 V/m

E Category: M4

Location: -5, -4, 8.7 mm



0 dB = 140.8 V/m = 42.97 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U3900-GSM850-190CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 61.27 V/m; Power Drift = -0.14 dB

PMF = 2.830 is applied.

E-field emissions = 135.8 V/m

Near-field category: M4 (AWF -5 dB)

PMF scaled E-field

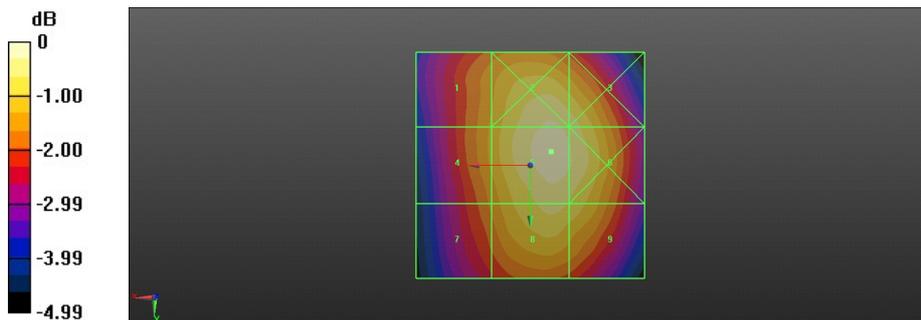
Grid 1 M4 119.7 V/m	Grid 2 M4 134.0 V/m	Grid 3 M4 131.5 V/m
Grid 4 M4 120.2 V/m	Grid 5 M4 135.8 V/m	Grid 6 M4 133.8 V/m
Grid 7 M4 115.5 V/m	Grid 8 M4 130.0 V/m	Grid 9 M4 127.8 V/m

Cursor:

Total = 135.8 V/m

E Category: M4

Location: -4.5, -3, 8.7 mm



0 dB = 138.3 V/m = 42.82 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U3900-GSM850-128CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 50.70 V/m; Power Drift = -0.05 dB

PMF = 2.830 is applied.

E-field emissions = 112.8 V/m

Near-field category: M4 (AWF -5 dB)

PMF scaled E-field

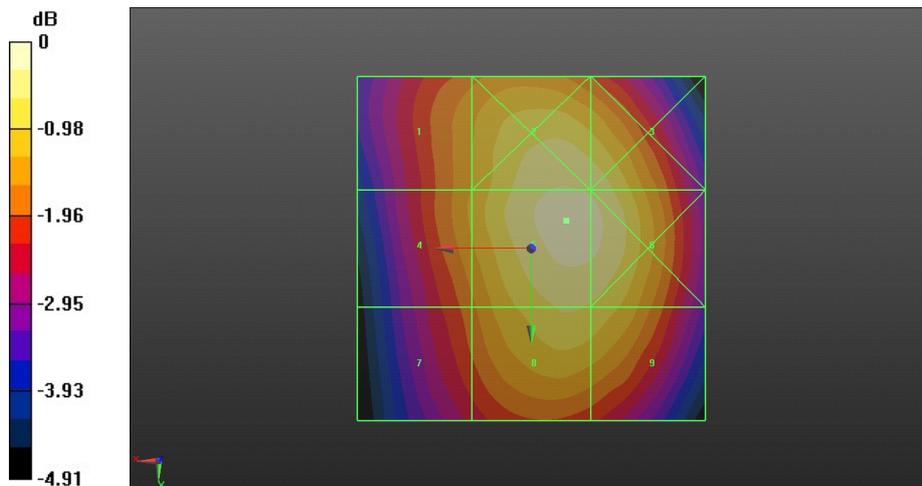
Grid 1 M4 99.19 V/m	Grid 2 M4 110.9 V/m	Grid 3 M4 110.1 V/m
Grid 4 M4 99.81 V/m	Grid 5 M4 112.8 V/m	Grid 6 M4 112.0 V/m
Grid 7 M4 94.35 V/m	Grid 8 M4 107.0 V/m	Grid 9 M4 106.1 V/m

Cursor:

Total = 112.8 V/m

E Category: M4

Location: -5, -4, 8.7 mm



0 dB = 114.8 V/m = 41.20 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U3900-GSM850-251CH-with battery 2#

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 60.28 V/m; Power Drift = 0.04 dB

PMF = 2.830 is applied.

E-field emissions = 134.3 V/m

Near-field category: M4 (AWF -5 dB)

PMF scaled E-field

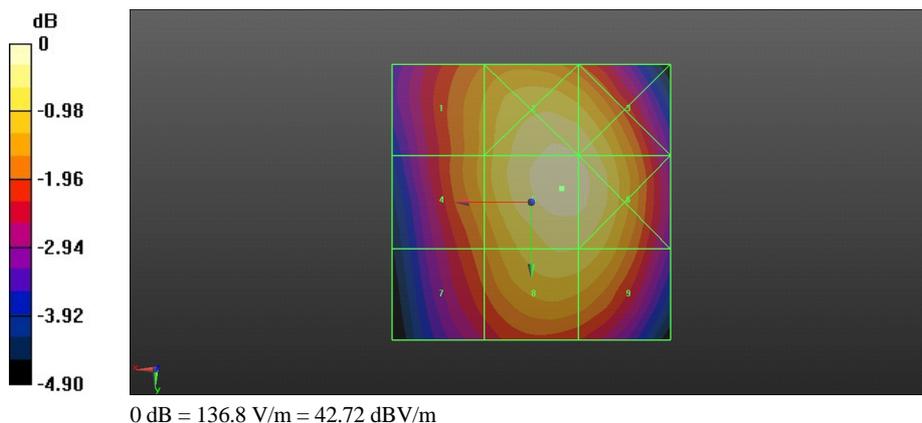
Grid 1 M4 119.6 V/m	Grid 2 M4 133.0 V/m	Grid 3 M4 131.6 V/m
Grid 4 M4 120.2 V/m	Grid 5 M4 134.3 V/m	Grid 6 M4 133.6 V/m
Grid 7 M4 113.3 V/m	Grid 8 M4 127.3 V/m	Grid 9 M4 126.6 V/m

Cursor:

Total = 134.3 V/m

E Category: M4

Location: -5.5, -2.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U3900-GSM850-251CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06500 A/m; Power Drift = 0.02 dB

PMF = 2.820 is applied.

H-field emissions = 0.2332 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

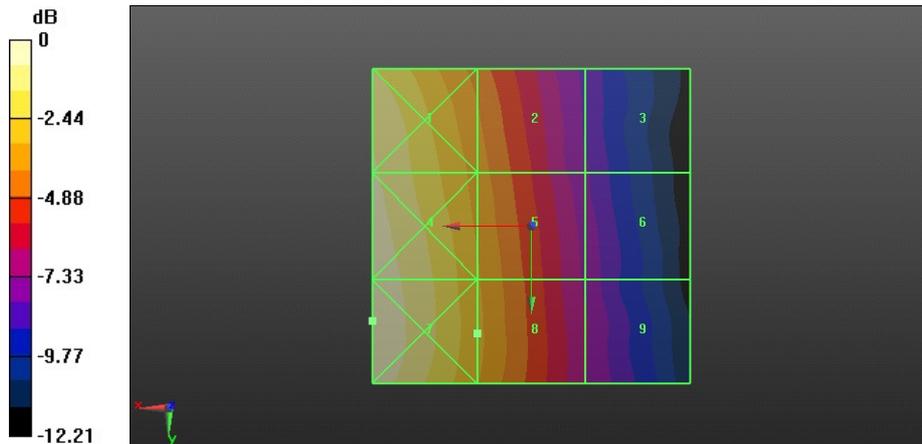
Grid 1 M4 0.305 A/m	Grid 2 M4 0.218 A/m	Grid 3 M4 0.132 A/m
Grid 4 M4 0.325 A/m	Grid 5 M4 0.230 A/m	Grid 6 M4 0.139 A/m
Grid 7 M4 0.330 A/m	Grid 8 M4 0.233 A/m	Grid 9 M4 0.144 A/m

Cursor:

Total = 0.3298 A/m

H Category: M4

Location: 25, 15, 8.7 mm



0 dB = 0.3298 A/m = -9.64 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U3900-GSM850-190CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06600 A/m; Power Drift = -0.08 dB

PMF = 2.820 is applied.

H-field emissions = 0.2279 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

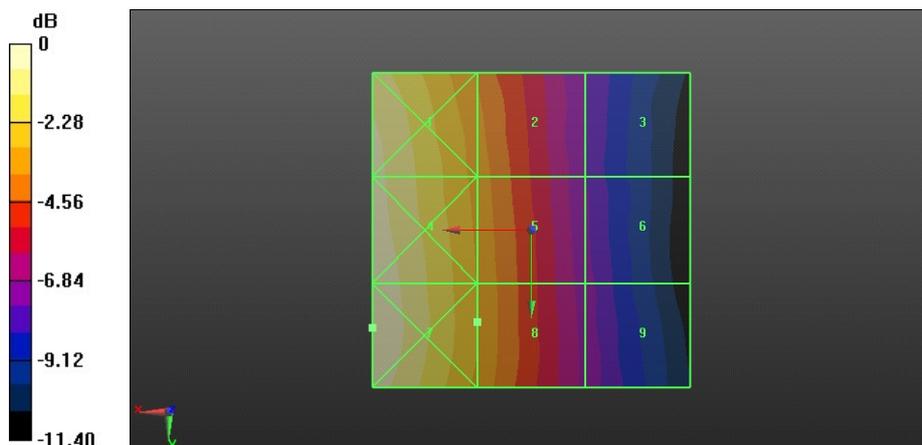
Grid 1 M4 0.306 A/m	Grid 2 M4 0.220 A/m	Grid 3 M4 0.136 A/m
Grid 4 M4 0.317 A/m	Grid 5 M4 0.227 A/m	Grid 6 M4 0.141 A/m
Grid 7 M4 0.323 A/m	Grid 8 M4 0.228 A/m	Grid 9 M4 0.144 A/m

Cursor:

Total = 0.3225 A/m

H Category: M4

Location: 25, 15.5, 8.7 mm



0 dB = 0.3225 A/m = -9.83 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U3900-GSM850-128CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05800 A/m; Power Drift = -0.04 dB

PMF = 2.820 is applied.

H-field emissions = 0.2017 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

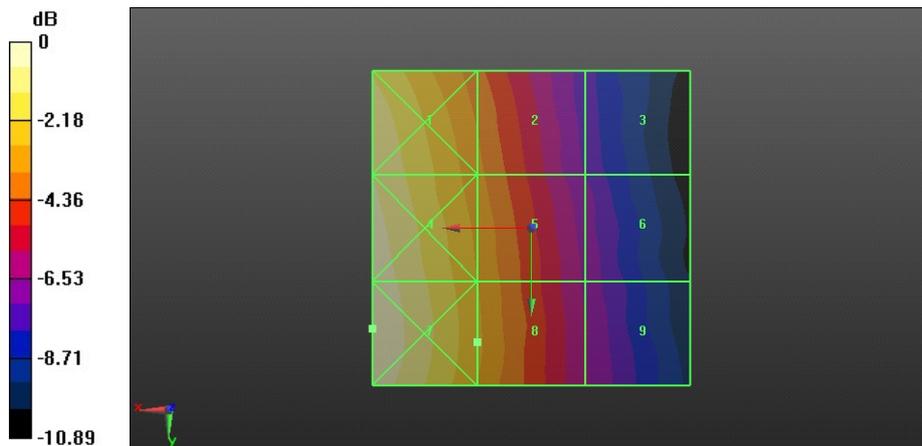
Grid 1 M4 0.254 A/m	Grid 2 M4 0.187 A/m	Grid 3 M4 0.120 A/m
Grid 4 M4 0.270 A/m	Grid 5 M4 0.199 A/m	Grid 6 M4 0.128 A/m
Grid 7 M4 0.276 A/m	Grid 8 M4 0.202 A/m	Grid 9 M4 0.133 A/m

Cursor:

Total = 0.2763 A/m

H Category: M4

Location: 25, 16, 8.7 mm



0 dB = 0.2763 A/m = -11.17 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U3900-GSM850-251CH-with battery 2#

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06500 A/m; Power Drift = -0.03 dB

PMF = 2.820 is applied.

H-field emissions = 0.2306 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

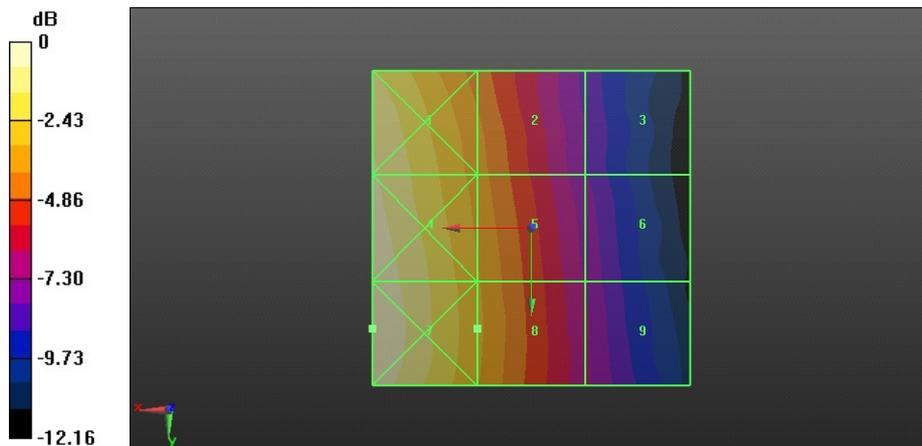
Grid 1 M4 0.303 A/m	Grid 2 M4 0.215 A/m	Grid 3 M4 0.130 A/m
Grid 4 M4 0.320 A/m	Grid 5 M4 0.228 A/m	Grid 6 M4 0.140 A/m
Grid 7 M4 0.327 A/m	Grid 8 M4 0.231 A/m	Grid 9 M4 0.145 A/m

Cursor:

Total = 0.3268 A/m

H Category: M4

Location: 25, 16, 8.7 mm



0 dB = 0.3268 A/m = -9.71 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U3900-GSM1900-810CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1909.8 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 13.89 V/m; Power Drift = 0.02 dB

PMF = 2.860 is applied.

E-field emissions = 48.13 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

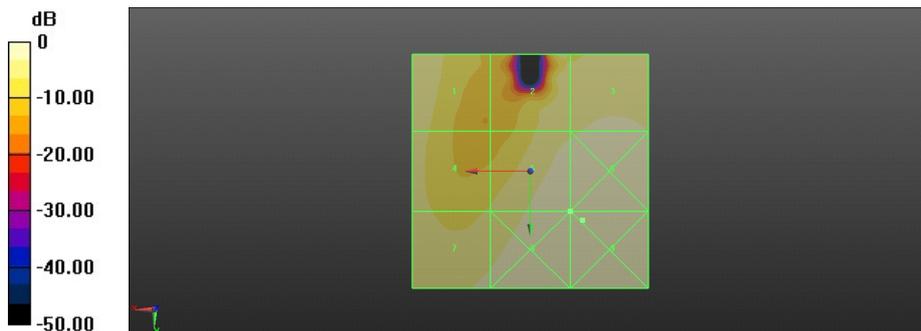
Grid 1 M4 30.68 V/m	Grid 2 M4 33.08 V/m	Grid 3 M4 37.29 V/m
Grid 4 M4 27.93 V/m	Grid 5 M3 48.13 V/m	Grid 6 M3 49.77 V/m
Grid 7 M4 37.41 V/m	Grid 8 M3 48.95 V/m	Grid 9 M3 50.32 V/m

Cursor:

Total = 50.32 V/m

E Category: M3

Location: -11, 10.5, 8.7 mm



0 dB = 50.69 V/m = 34.10 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U3900-GSM1900-661CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 14.73 V/m; Power Drift = 0.14 dB

PMF = 2.860 is applied.

E-field emissions = 51.16 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

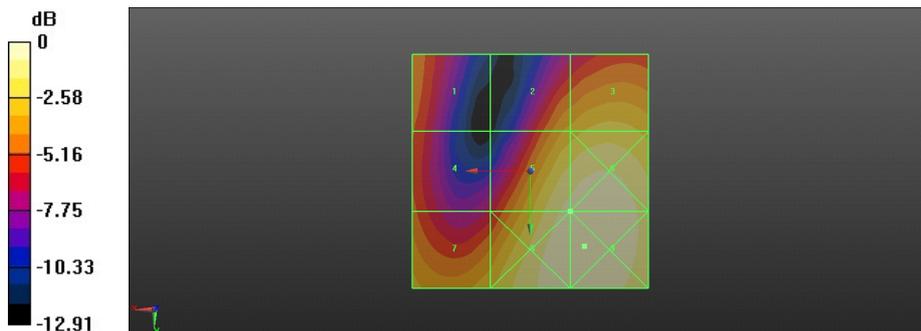
Grid 1 M4 32.66 V/m	Grid 2 M4 38.25 V/m	Grid 3 M4 42.50 V/m
Grid 4 M4 31.45 V/m	Grid 5 M3 51.16 V/m	Grid 6 M3 52.98 V/m
Grid 7 M4 40.01 V/m	Grid 8 M3 53.41 V/m	Grid 9 M3 54.07 V/m

Cursor:

Total = 54.07 V/m

E Category: M3

Location: -11.5, 16, 8.7 mm



0 dB = 54.46 V/m = 34.72 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U3900-GSM1900-512CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 17.26 V/m; Power Drift = -0.03 dB

PMF = 2.860 is applied.

E-field emissions = 55.59 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

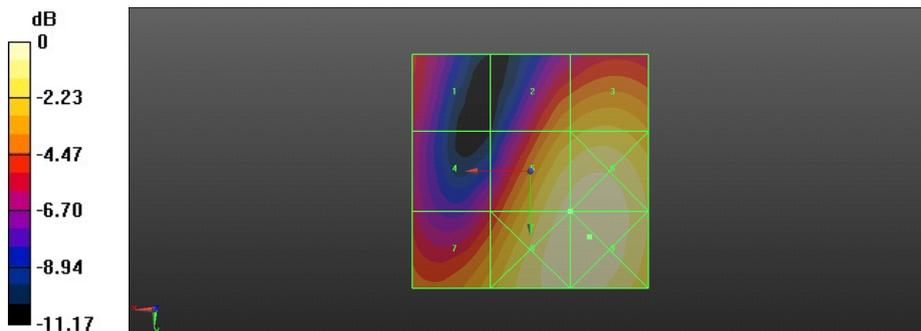
Grid 1 M4 32.90 V/m	Grid 2 M4 42.98 V/m	Grid 3 M4 46.37 V/m
Grid 4 M4 30.72 V/m	Grid 5 M3 55.59 V/m	Grid 6 M3 57.22 V/m
Grid 7 M4 43.57 V/m	Grid 8 M3 57.12 V/m	Grid 9 M3 57.87 V/m

Cursor:

Total = 57.86 V/m

E Category: M3

Location: -12.5, 14, 8.7 mm



0 dB = 58.29 V/m = 35.31 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U3900-GSM1900-512CH-with battery 2#

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 20.81 V/m; Power Drift = -0.01 dB

PMF = 2.860 is applied.

E-field emissions = 64.52 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

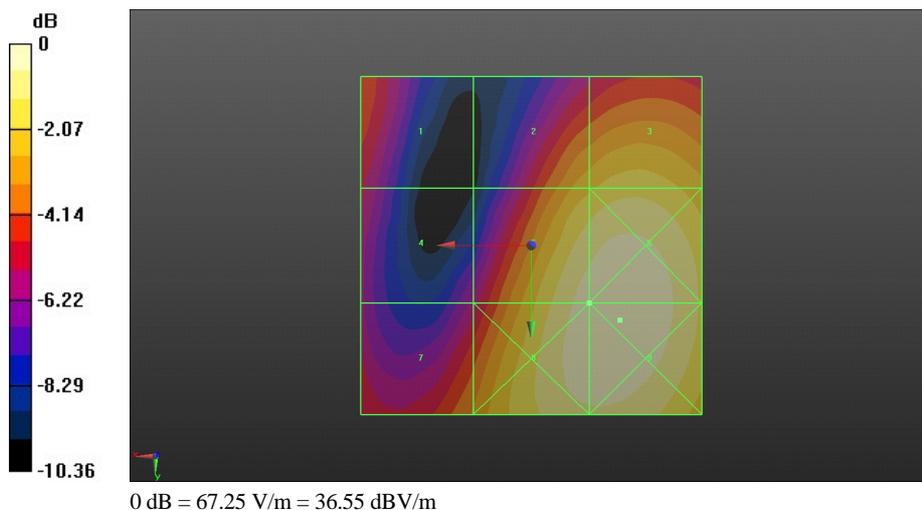
Grid 1 M4 41.63 V/m	Grid 2 M3 52.14 V/m	Grid 3 M3 56.00 V/m
Grid 4 M4 36.34 V/m	Grid 5 M3 64.52 V/m	Grid 6 M3 66.62 V/m
Grid 7 M4 45.85 V/m	Grid 8 M3 65.28 V/m	Grid 9 M3 66.76 V/m

Cursor:

Total = 66.76 V/m

E Category: M3

Location: -13, 11, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U3900-GSM1900-810CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1909.8 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05100 A/m; Power Drift = -0.06 dB

PMF = 2.830 is applied.

H-field emissions = 0.1584 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

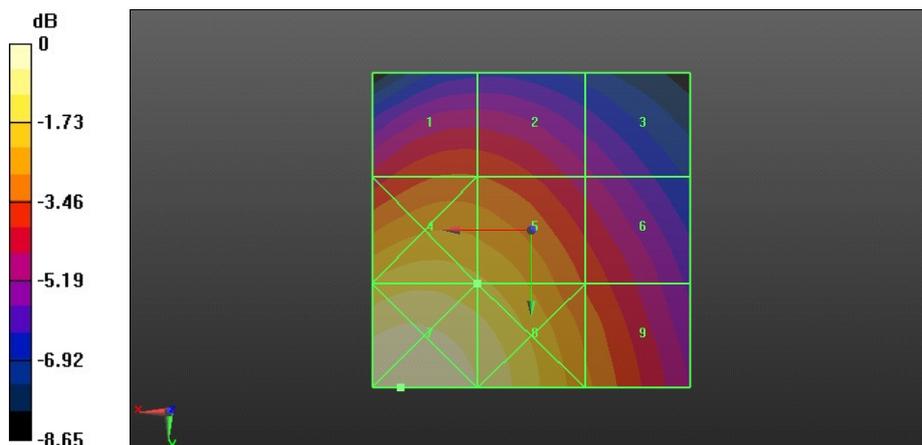
Grid 1 M4 0.129 A/m	Grid 2 M4 0.128 A/m	Grid 3 M4 0.107 A/m
Grid 4 M3 0.164 A/m	Grid 5 M3 0.158 A/m	Grid 6 M4 0.127 A/m
Grid 7 M3 0.190 A/m	Grid 8 M3 0.178 A/m	Grid 9 M4 0.139 A/m

Cursor:

Total = 0.1899 A/m

H Category: M3

Location: 20.5, 25, 8.7 mm



0 dB = 0.1899 A/m = -14.43 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U3900-GSM1900-661CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05300 A/m; Power Drift = 0.01 dB

PMF = 2.830 is applied.

H-field emissions = 0.1665 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

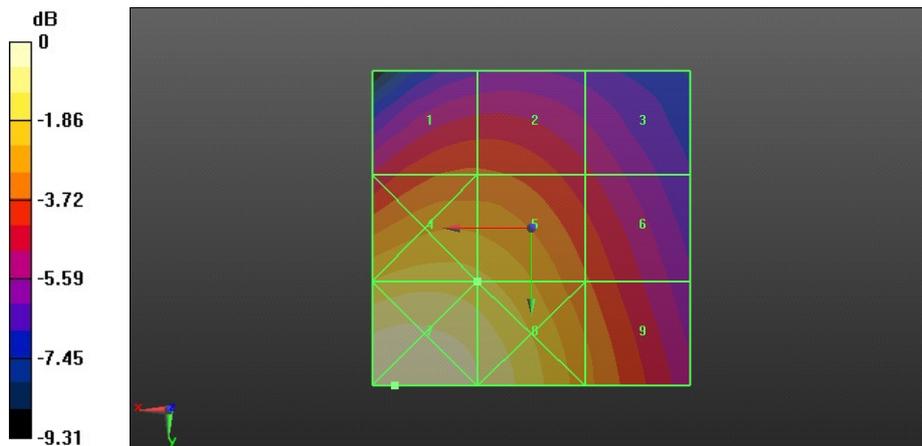
Grid 1 M4 0.133 A/m	Grid 2 M4 0.133 A/m	Grid 3 M4 0.116 A/m
Grid 4 M3 0.170 A/m	Grid 5 M3 0.166 A/m	Grid 6 M4 0.133 A/m
Grid 7 M3 0.201 A/m	Grid 8 M3 0.188 A/m	Grid 9 M3 0.144 A/m

Cursor:

Total = 0.2012 A/m

H Category: M3

Location: 21.5, 25, 8.7 mm



0 dB = 0.2012 A/m = -13.93 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U3900-GSM1900-512CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05100 A/m; Power Drift = -0.02 dB

PMF = 2.830 is applied.

H-field emissions = 0.1637 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

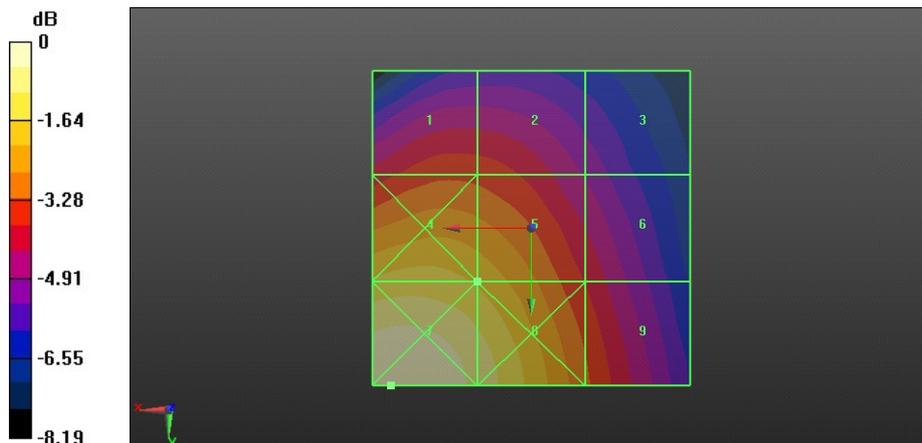
Grid 1 M4 0.135 A/m	Grid 2 M4 0.134 A/m	Grid 3 M4 0.113 A/m
Grid 4 M3 0.171 A/m	Grid 5 M3 0.164 A/m	Grid 6 M4 0.128 A/m
Grid 7 M3 0.199 A/m	Grid 8 M3 0.184 A/m	Grid 9 M4 0.139 A/m

Cursor:

Total = 0.1994 A/m

H Category: M3

Location: 22, 25, 8.7 mm



0 dB = 0.1994 A/m = -14.01 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U3900-GSM1900-661CH-with battery 2#

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05800 A/m; Power Drift = 0.06 dB

PMF = 2.830 is applied.

H-field emissions = 0.1830 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

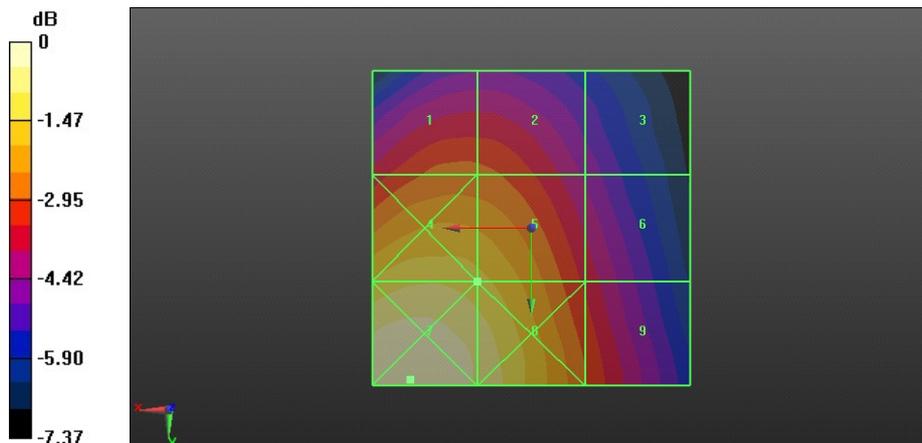
Grid 1 M3 0.155 A/m	Grid 2 M3 0.154 A/m	Grid 3 M4 0.126 A/m
Grid 4 M3 0.189 A/m	Grid 5 M3 0.183 A/m	Grid 6 M3 0.141 A/m
Grid 7 M3 0.212 A/m	Grid 8 M3 0.199 A/m	Grid 9 M3 0.152 A/m

Cursor:

Total = 0.2120 A/m

H Category: M3

Location: 19, 24, 8.7 mm



0 dB = 0.2120 A/m = -13.47 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U3900-UMTS Band V-4233CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 54.13 V/m; Power Drift = 0.03 dB

PMF = 1.040 is applied.

E-field emissions = 45.50 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

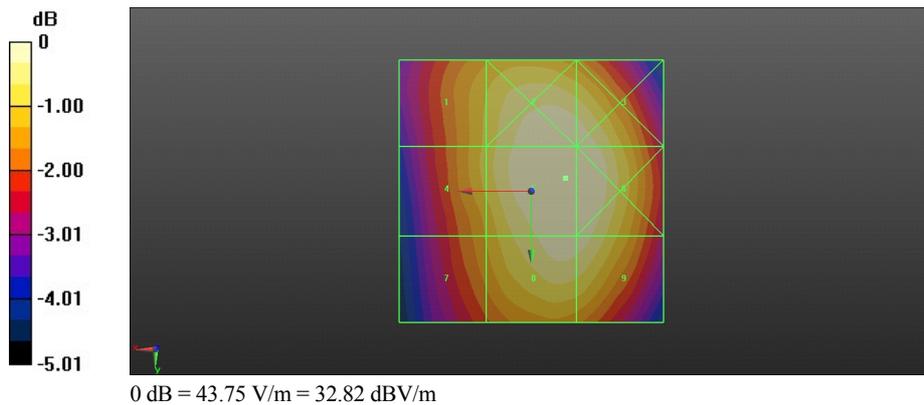
Grid 1 M4 39.54 V/m	Grid 2 M4 44.73 V/m	Grid 3 M4 44.05 V/m
Grid 4 M4 39.78 V/m	Grid 5 M4 45.50 V/m	Grid 6 M4 45.33 V/m
Grid 7 M4 37.72 V/m	Grid 8 M4 43.42 V/m	Grid 9 M4 43.21 V/m

Cursor:

Total = 45.50 V/m

E Category: M4

Location: -6.5, -2.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U3900-UMTS Band V-4182CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 836.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 44.55 V/m; Power Drift = -0.04 dB

PMF = 1.040 is applied.

E-field emissions = 37.04 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

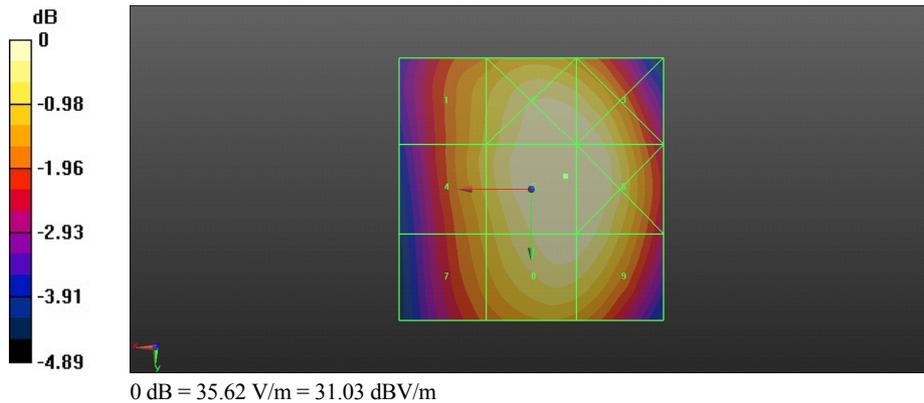
Grid 1 M4 32.21 V/m	Grid 2 M4 36.36 V/m	Grid 3 M4 36.17 V/m
Grid 4 M4 32.53 V/m	Grid 5 M4 37.04 V/m	Grid 6 M4 36.91 V/m
Grid 7 M4 31.22 V/m	Grid 8 M4 35.57 V/m	Grid 9 M4 35.41 V/m

Cursor:

Total = 37.04 V/m

E Category: M4

Location: -6.5, -2.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U3900-UMTS Band V-4132CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 826.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 46.29 V/m; Power Drift = 0.02 dB

PMF = 1.040 is applied.

E-field emissions = 39.08 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

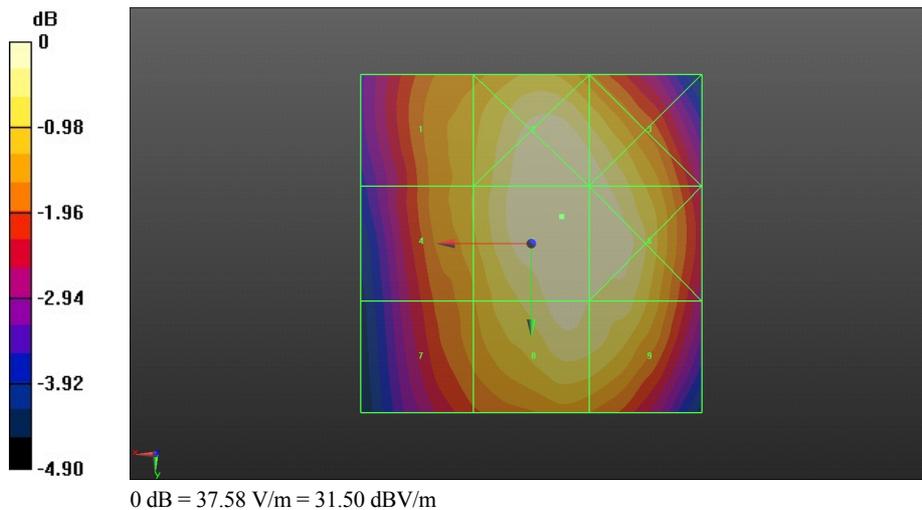
Grid 1 M4 33.58 V/m	Grid 2 M4 38.69 V/m	Grid 3 M4 37.49 V/m
Grid 4 M4 33.72 V/m	Grid 5 M4 39.08 V/m	Grid 6 M4 38.13 V/m
Grid 7 M4 32.24 V/m	Grid 8 M4 37.13 V/m	Grid 9 M4 36.21 V/m

Cursor:

Total = 39.08 V/m

E Category: M4

Location: -4.5, -4, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U3900-UMTS Band V-4233CH-with battery 2#

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 846.6MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 55.17 V/m; Power Drift = -0.00 dB

PMF = 1.040 is applied.

E-field emissions = 45.32 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

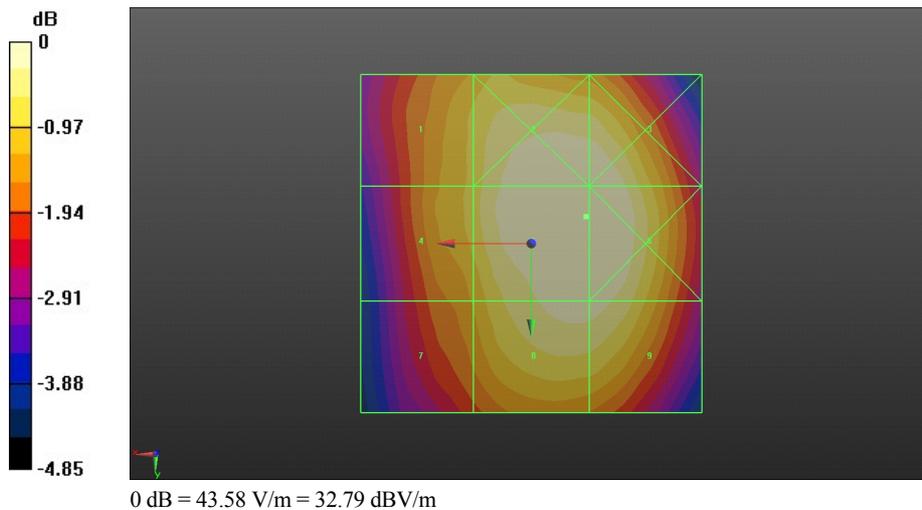
Grid 1 M4 39.65 V/m	Grid 2 M4 44.51 V/m	Grid 3 M4 44.49 V/m
Grid 4 M4 39.80 V/m	Grid 5 M4 45.32 V/m	Grid 6 M4 45.32 V/m
Grid 7 M4 37.78 V/m	Grid 8 M4 42.91 V/m	Grid 9 M4 42.88 V/m

Cursor:

Total = 45.32 V/m

E Category: M4

Location: -8, -4, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U3900-UMTS Band V-4233CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06100 A/m; Power Drift = -0.11 dB

PMF = 1.020 is applied.

H-field emissions = 0.07586 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

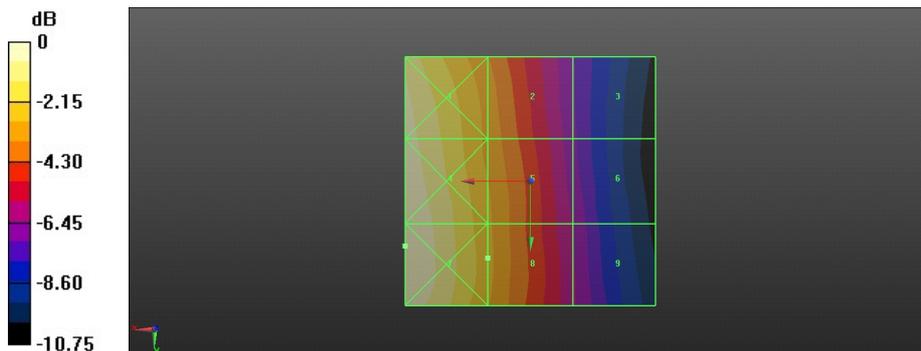
Grid 1 M4 0.098 A/m	Grid 2 M4 0.072 A/m	Grid 3 M4 0.046 A/m
Grid 4 M4 0.104 A/m	Grid 5 M4 0.075 A/m	Grid 6 M4 0.049 A/m
Grid 7 M4 0.104 A/m	Grid 8 M4 0.076 A/m	Grid 9 M4 0.050 A/m

Cursor:

Total = 0.1044 A/m

H Category: M4

Location: 25, 13, 8.7 mm



0 dB = 0.1024 A/m = -19.79 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U3900-UMTS Band V-4182CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 836.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05100 A/m; Power Drift = 0.13 dB

PMF = 1.020 is applied.

H-field emissions = 0.06334 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

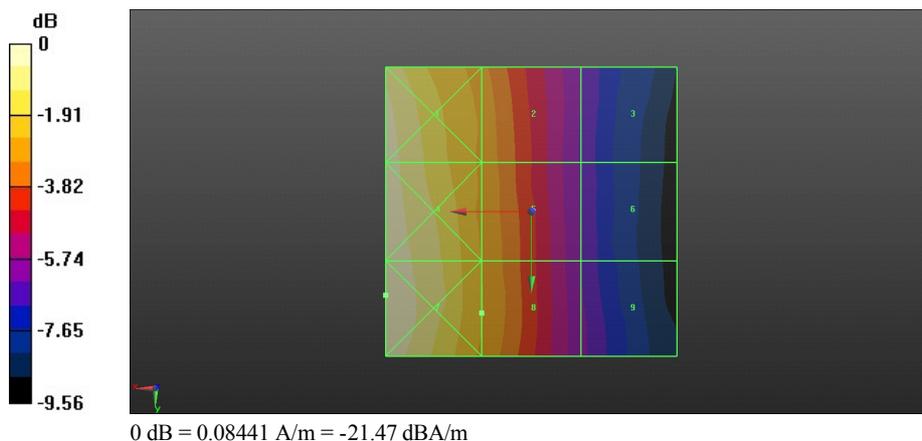
Grid 1 M4 0.082 A/m	Grid 2 M4 0.062 A/m	Grid 3 M4 0.041 A/m
Grid 4 M4 0.085 A/m	Grid 5 M4 0.063 A/m	Grid 6 M4 0.041 A/m
Grid 7 M4 0.086 A/m	Grid 8 M4 0.063 A/m	Grid 9 M4 0.042 A/m

Cursor:

Total = 0.08609 A/m

H Category: M4

Location: 25, 14.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U3900-UMTS Band V-4132CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 826.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05500 A/m; Power Drift = 0.01 dB

PMF = 1.020 is applied.

H-field emissions = 0.06901 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

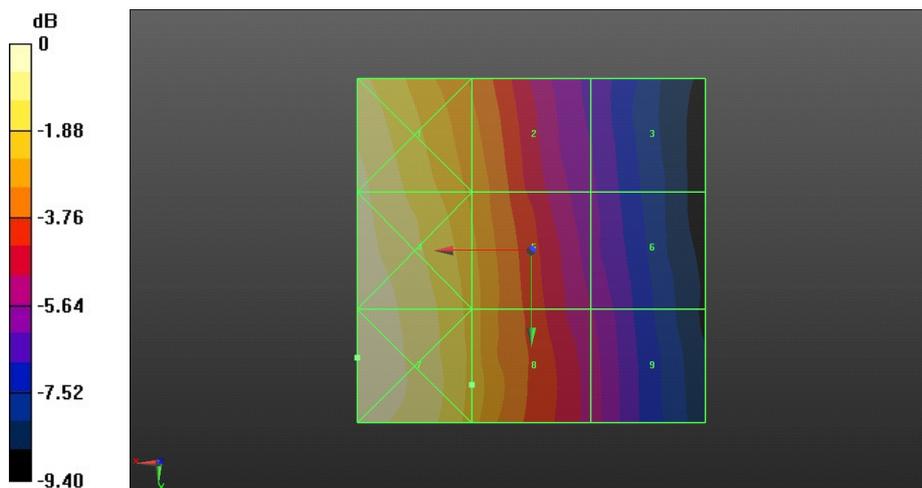
Grid 1 M4 0.084 A/m	Grid 2 M4 0.065 A/m	Grid 3 M4 0.043 A/m
Grid 4 M4 0.088 A/m	Grid 5 M4 0.068 A/m	Grid 6 M4 0.046 A/m
Grid 7 M4 0.089 A/m	Grid 8 M4 0.069 A/m	Grid 9 M4 0.048 A/m

Cursor:

Total = 0.08937 A/m

H Category: M4

Location: 25, 15.5, 8.7 mm



0 dB = 0.08762 A/m = -21.15 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U3900-UMTS Band V-4233CH-with battery 2#

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06200 A/m; Power Drift = -0.14 dB

PMF = 1.020 is applied.

H-field emissions = 0.07788 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

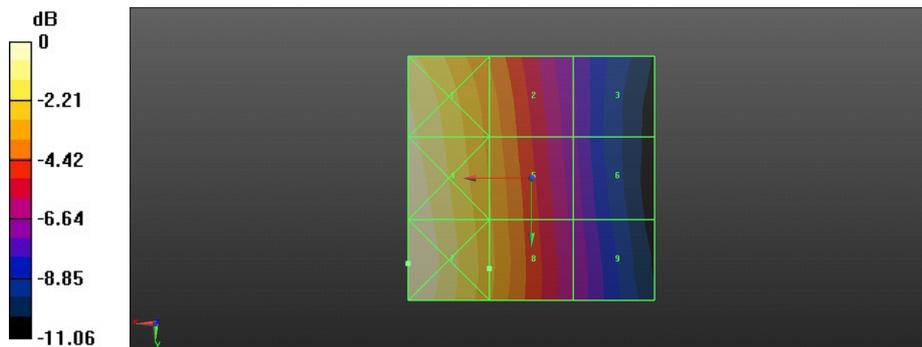
Grid 1 M4 0.100 A/m	Grid 2 M4 0.074 A/m	Grid 3 M4 0.047 A/m
Grid 4 M4 0.105 A/m	Grid 5 M4 0.077 A/m	Grid 6 M4 0.048 A/m
Grid 7 M4 0.108 A/m	Grid 8 M4 0.078 A/m	Grid 9 M4 0.050 A/m

Cursor:

Total = 0.1082 A/m

H Category: M4

Location: 25, 17.5, 8.7 mm



0 dB = 0.1061 A/m = -19.49 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U3900-UMTS Band II-9538CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1907.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 17.27 V/m; Power Drift = 0.07 dB

PMF = 1.020 is applied.

E-field emissions = 19.97 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

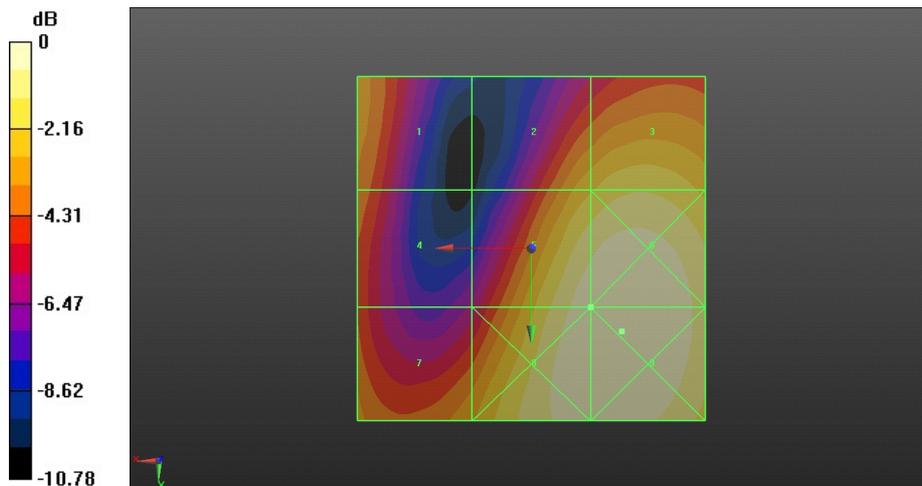
Grid 1 M4 14.13 V/m	Grid 2 M4 15.81 V/m	Grid 3 M4 17.29 V/m
Grid 4 M4 13.17 V/m	Grid 5 M4 19.97 V/m	Grid 6 M4 20.76 V/m
Grid 7 M4 14.57 V/m	Grid 8 M4 20.39 V/m	Grid 9 M4 20.88 V/m

Cursor:

Total = 20.88 V/m

E Category: M4

Location: -13, 12, 8.7 mm



0 dB = 20.47 V/m = 26.22 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U3900-UMTS Band II-9400CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 19.76 V/m; Power Drift = 0.06 dB

PMF = 1.020 is applied.

E-field emissions = 23.46 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

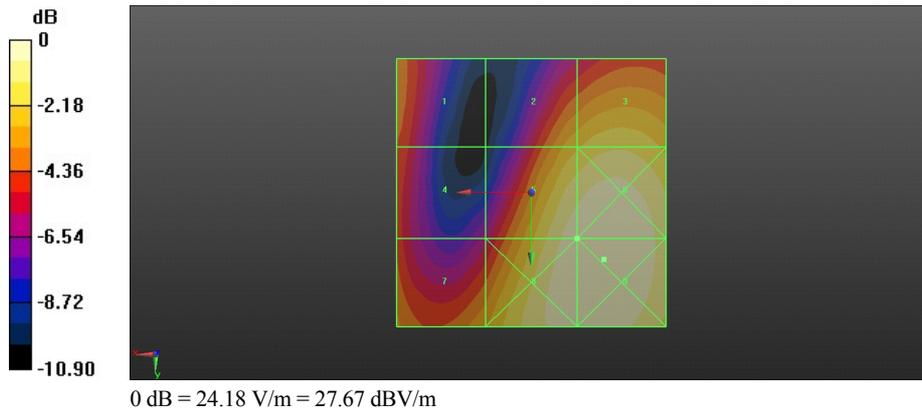
Grid 1 M4 15.61 V/m	Grid 2 M4 18.59 V/m	Grid 3 M4 20.28 V/m
Grid 4 M4 14.73 V/m	Grid 5 M4 23.45 V/m	Grid 6 M4 24.49 V/m
Grid 7 M4 17.24 V/m	Grid 8 M4 24.08 V/m	Grid 9 M4 24.66 V/m

Cursor:

Total = 24.66 V/m

E Category: M4

Location: -13.5, 12.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U3900-UMTS Band II-9262CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 26.18 V/m; Power Drift = 0.03 dB

PMF = 1.020 is applied.

E-field emissions = 29.95 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

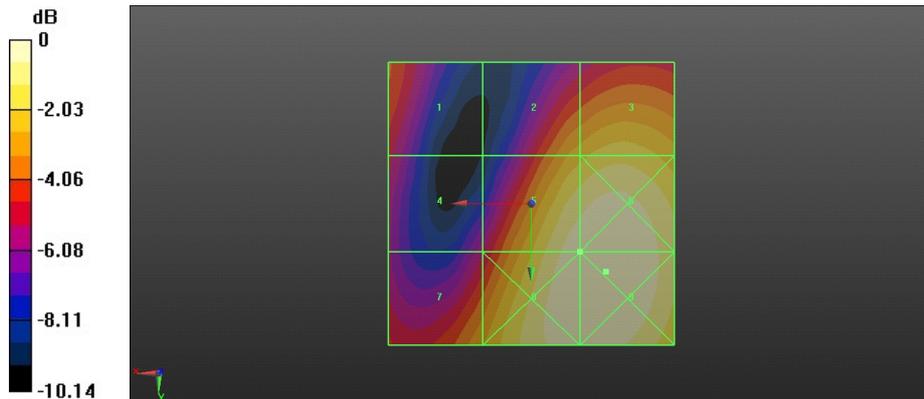
Grid 1 M4 19.53 V/m	Grid 2 M4 23.55 V/m	Grid 3 M4 25.50 V/m
Grid 4 M4 17.08 V/m	Grid 5 M4 29.95 V/m	Grid 6 M4 31.01 V/m
Grid 7 M4 22.33 V/m	Grid 8 M4 30.69 V/m	Grid 9 M4 31.22 V/m

Cursor:

Total = 31.22 V/m

E Category: M4

Location: -13, 12, 8.7 mm



0 dB = 30.61 V/m = 29.72 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U3900-UMTS Band II-9262CH-with battery 2#

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 28.61 V/m; Power Drift = 0.01 dB

PMF = 1.020 is applied.

E-field emissions = 29.82 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

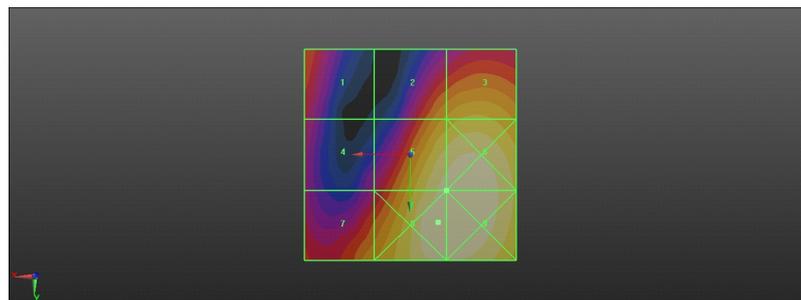
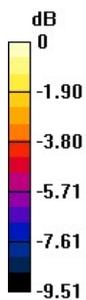
Grid 1 M4 20.12 V/m	Grid 2 M4 23.60 V/m	Grid 3 M4 25.44 V/m
Grid 4 M4 17.82 V/m	Grid 5 M4 29.82 V/m	Grid 6 M4 30.80 V/m
Grid 7 M4 23.19 V/m	Grid 8 M4 31.61 V/m	Grid 9 M4 31.04 V/m

Cursor:

Total = 31.61 V/m

E Category: M4

Location: -6.5, 16, 8.7 mm



0 dB = 30.99 V/m = 29.82 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U3900-UMTS Band II-9538CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1907.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06000 A/m; Power Drift = 0.01 dB

PMF = 1.010 is applied.

H-field emissions = 0.06657 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

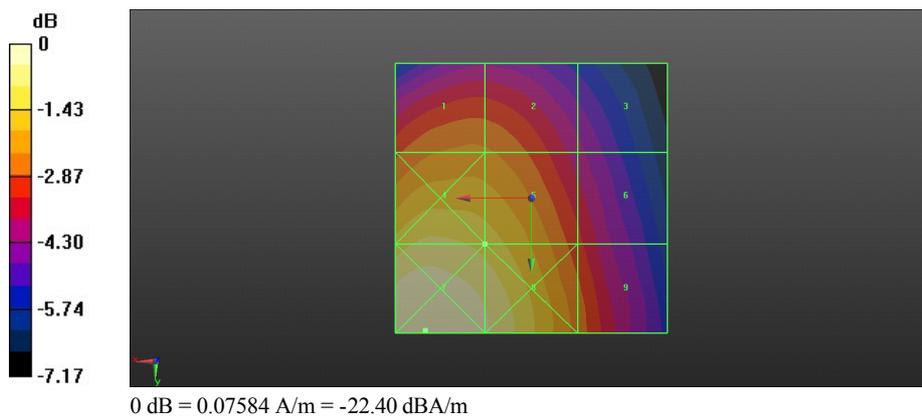
Grid 1 M4 0.059 A/m	Grid 2 M4 0.058 A/m	Grid 3 M4 0.047 A/m
Grid 4 M4 0.069 A/m	Grid 5 M4 0.067 A/m	Grid 6 M4 0.053 A/m
Grid 7 M4 0.077 A/m	Grid 8 M4 0.072 A/m	Grid 9 M4 0.056 A/m

Cursor:

Total = 0.07660 A/m

H Category: M4

Location: 19.5, 24.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U3900-UMTS Band II-9400CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06700 A/m; Power Drift = 0.02 dB

PMF = 1.010 is applied.

H-field emissions = 0.07313 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

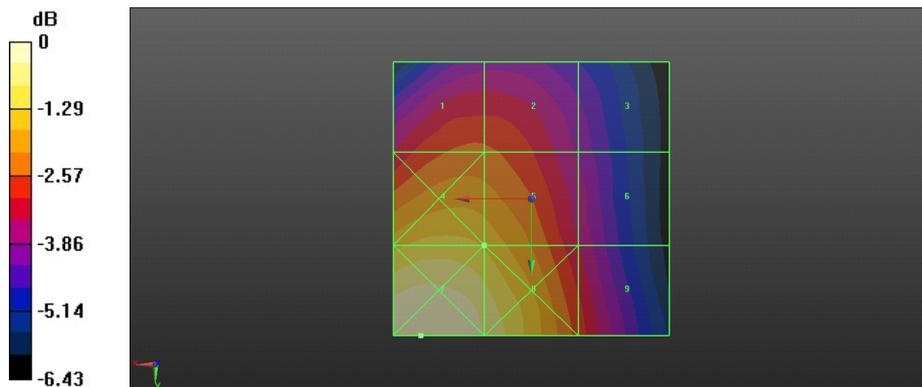
Grid 1 M4 0.064 A/m	Grid 2 M4 0.064 A/m	Grid 3 M4 0.054 A/m
Grid 4 M4 0.075 A/m	Grid 5 M4 0.073 A/m	Grid 6 M4 0.058 A/m
Grid 7 M4 0.086 A/m	Grid 8 M4 0.081 A/m	Grid 9 M4 0.062 A/m

Cursor:

Total = 0.08620 A/m

H Category: M4

Location: 20, 25, 8.7 mm



0 dB = 0.08535 A/m = -21.38 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U3900-UMTS Band II-9262CH

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz; Duty Cycle: 1:1
 Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
 Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

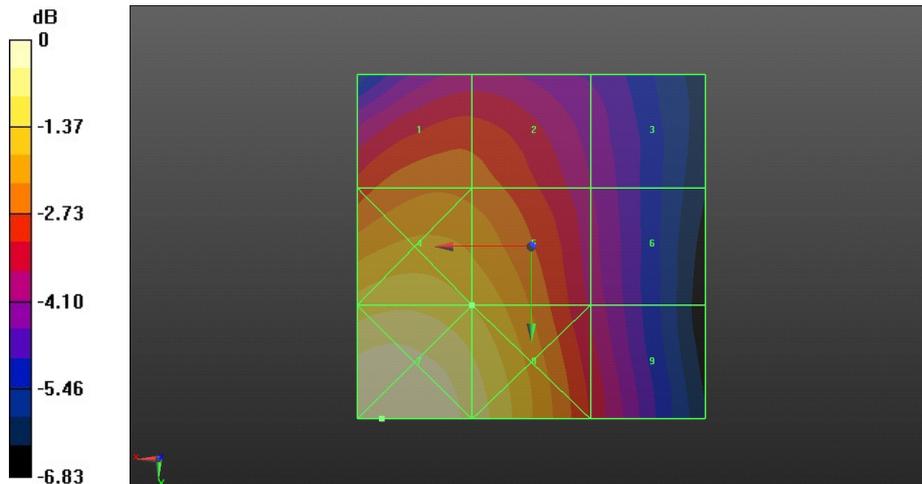
Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.07800 A/m; Power Drift = -0.03 dB
 PMF = 1.010 is applied.
 H-field emissions = 0.08718 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.078 A/m	Grid 2 M4 0.077 A/m	Grid 3 M4 0.064 A/m
Grid 4 M4 0.091 A/m	Grid 5 M4 0.087 A/m	Grid 6 M4 0.067 A/m
Grid 7 M4 0.103 A/m	Grid 8 M4 0.095 A/m	Grid 9 M4 0.071 A/m

Cursor:
 Total = 0.1032 A/m
 H Category: M4
 Location: 21.5, 25, 8.7 mm



0 dB = 0.1021 A/m = -19.82 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U3900-UMTS Band II-9262CH-with battery 2#

DUT: U3900; Type: HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08400 A/m; Power Drift = -0.04 dB

PMF = 1.010 is applied.

H-field emissions = 0.09230 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

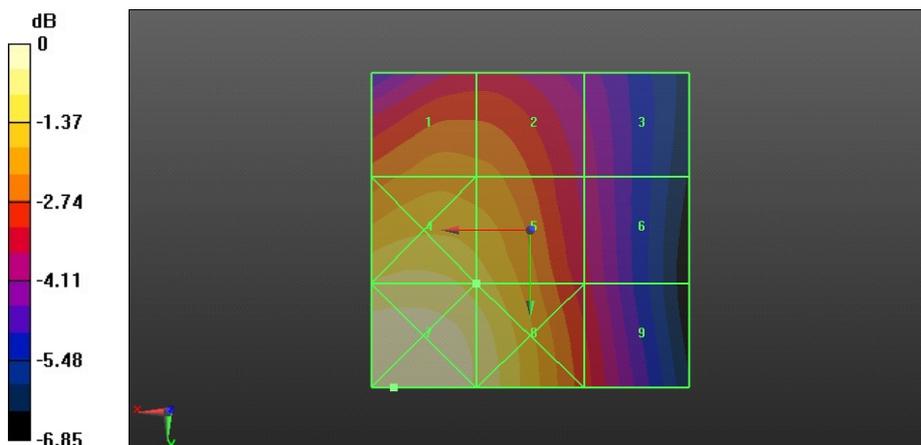
Grid 1 M4 0.083 A/m	Grid 2 M4 0.082 A/m	Grid 3 M4 0.068 A/m
Grid 4 M4 0.096 A/m	Grid 5 M4 0.092 A/m	Grid 6 M4 0.070 A/m
Grid 7 M4 0.106 A/m	Grid 8 M4 0.099 A/m	Grid 9 M4 0.074 A/m

Cursor:

Total = 0.1057 A/m

H Category: M4

Location: 21.5, 25, 8.7 mm



0 dB = 0.1047 A/m = -19.60 dBA/m